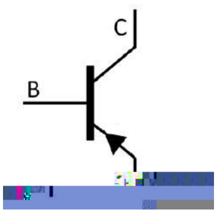
VRW0656 ṂṂ Ŀ SQS ᴁṀ ɥ s ǁ ᒣ Silicon PNP transistor in a SOT-323 Plastic Package.

ؤ ﬤ ǁ´ ╙ ﬤ ╙ ﺯ ι ت ᵓ я ں Ң ι љ 5VF4:74 Z Ӣ ´

Large I_c low $V_{ce(sat)}$



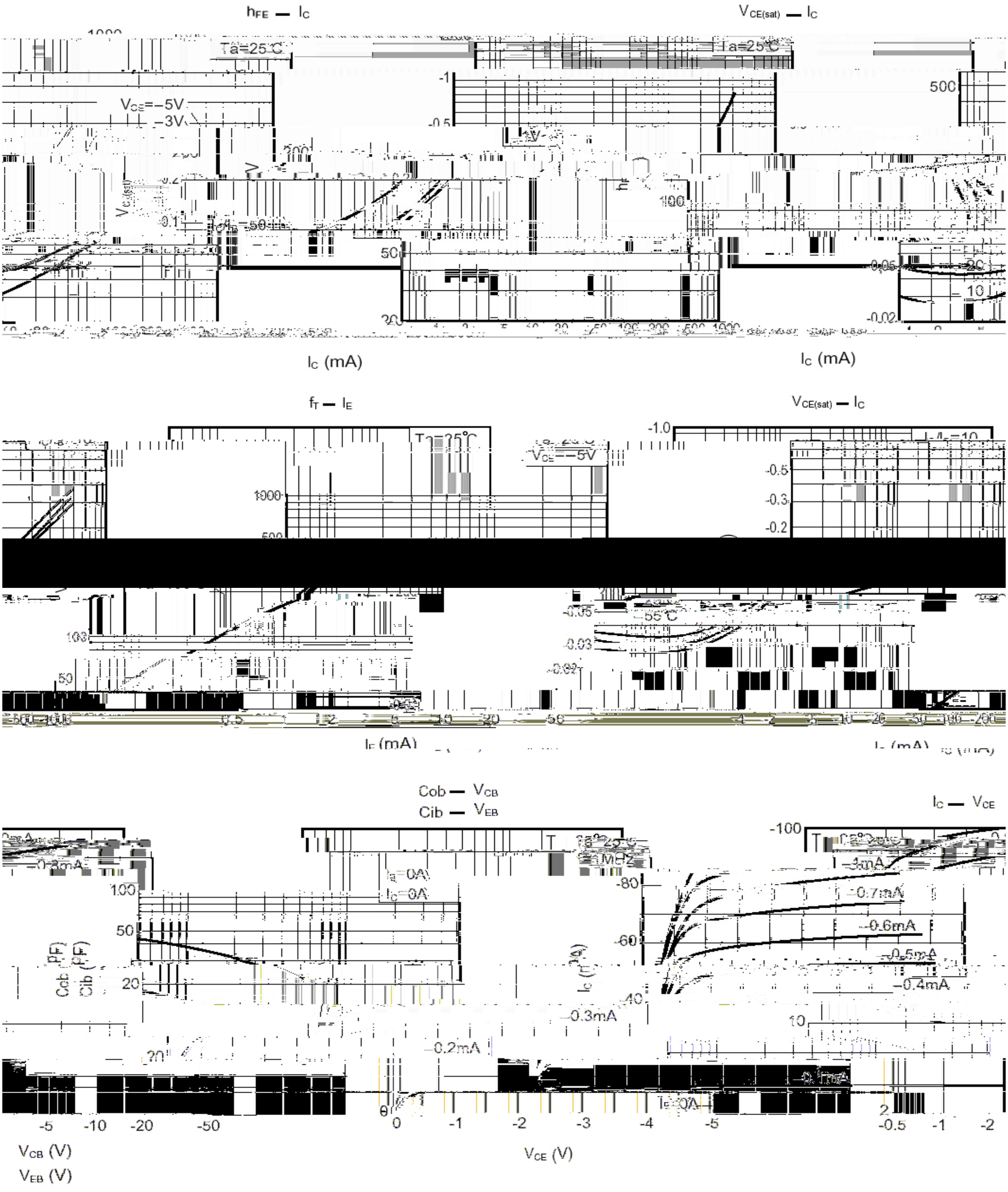
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-32	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-100μA	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA	-32			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-100μA	-5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-20V			-1.0	μA
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=-4.0V			-1.0	μA
DC Current Gain	h_{FE}	V_{CE}=-3.0V I_C=-10mA	82		390	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-100mA I_B=-10mA			-0.4	V
Transition Frequency	f_T	V_{CE}=-5.0V I_E=20mA f=100MHz		200		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V I_E=0 f=1.0MHz		7.0		pF

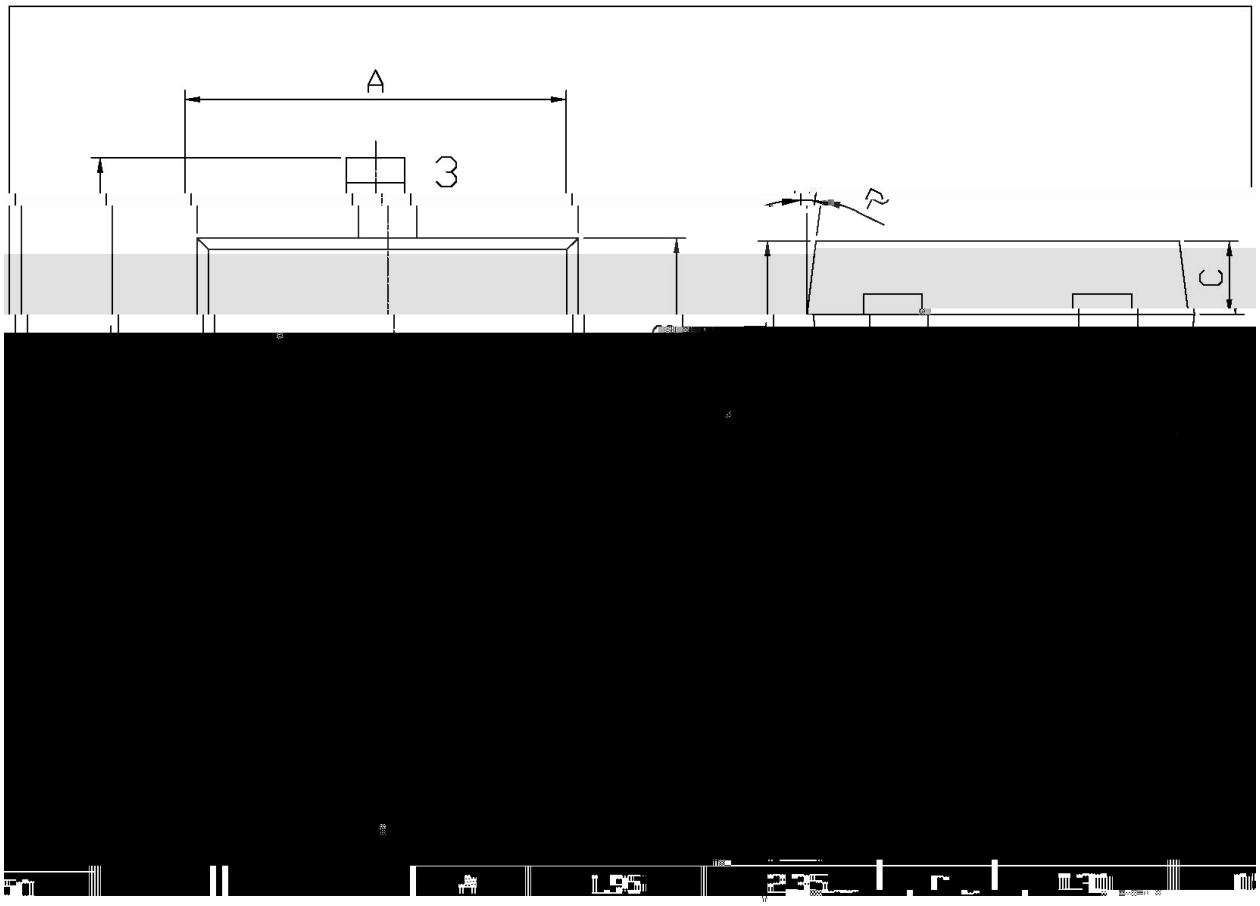
/ Electrical Characteristic Curve



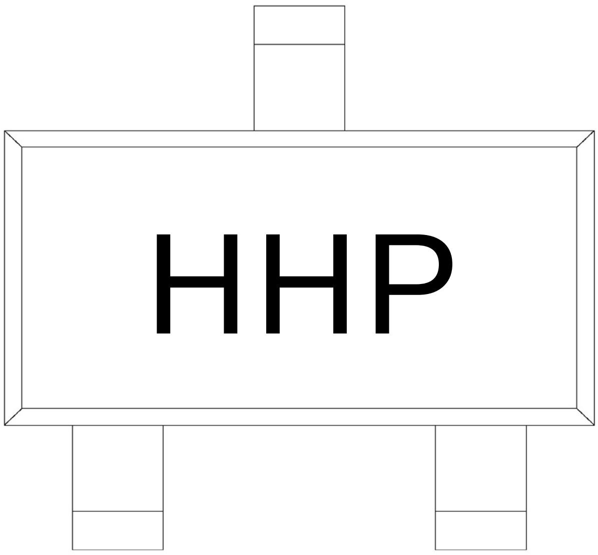
ᵘ ĖÒĻ ʃ / Package Dimensions

SOT-323

单位：mm



ŧ˛ Ł˝Ω / Marking Instructions



ب ˝ χ

H χ ㅬ ३ ᴻ Ꮒ

H χ ㅬ ʒ ᴺ Ꮒ

P χ ㅬ h_{FE} ˂ ⁶ Ꮒ

Note:

H: Company Code.

H: Product Type.

P χ h_{FE} Classifications Symbol